# RT1N137P

TRANSISTOR WITH RESISTOR FOR SWITCHING APPLICATION SILICON NPN EPITAXIAL TYPE

### DESCRIPTION

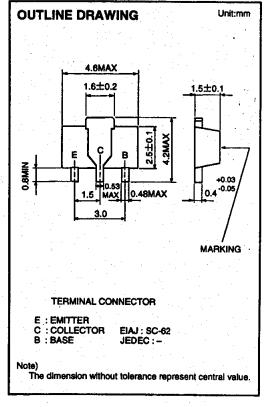
AT1N137P is a one chip transistor with built-in bias resistor, PNP type is RT1P137P.

#### **FEATURE**

- Built-in bias resistor (R₁=1kΩ,R₂=22kΩ)
- ●Low VCE(sat) VCE(sat)=0.3Vmax (@IC=300mA,Ia=3mA)
- ●High collector dissipation Pc=500mW

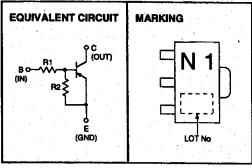
### **APPLICATION**

Inverted circuit, switching circuit, interface circuit, driver circuit.



# MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit	
Vсво	Collector to Base voltage	40	V	
VEBO	Emitter to Base voltage	6	V	
VCEO	Collector to Ernitter voltage	40	V	
lc	Collector current	1	A	
lcм	Peak Collector current	2	Α	
Pc	Collector dissipation(Ta=25°C) 500		mW	
Tj	Junction temperature	+150	°C	
Tstg	Storage temperature	-55 to +150	·c	



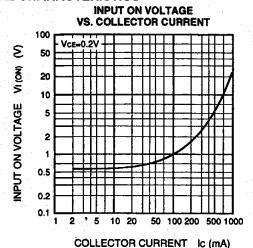
### ELECTRICAL CHARACTERISTICS (Ta=25°C)

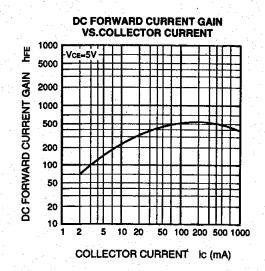
Symbol	Parameter	Test conditions	Limits			l Imia
			Min	Тур	Max	Unit
V(BR)CEO	C to E break down voltage	Ic=1mA,R <sub>BE</sub> =∞	40	I		V
Ісво	Collector cut off current	VCB=40V,IE=0			0.1	μΑ
hfe	DC forward current gain	VcE=6V,Ic=100mA	100			
VCE(sat)	C to E saturation voltage	Ic=300mA,is=3mA		0.1	0.3	٧
VI(ON)	Input on voltage	VcE=0.2V,lc=300mA	T	2.3	4.0	V
VI(OFF)	Input off voltage	VcE=5V,lc=100 μ A	0.4	0.5		V
R1	Input resistor		0.7	1.0	1.3	kΩ
R2/R1	Resistor ratio		20	22	24	
fr	Gain band width product	Vce=6V,Ie=-10mA	1	150		MHz

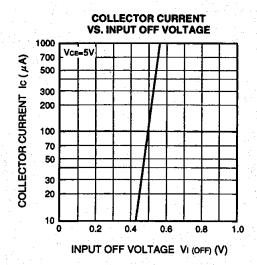
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### **TYPICAL CHARACTERISTICS**









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